

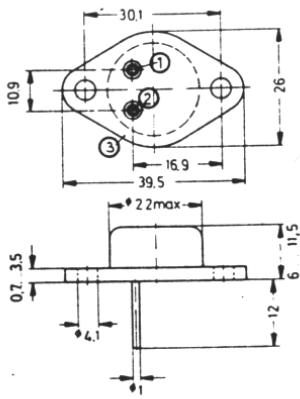
IRF 244
MOS-FET N-Channel enhanced

Text: V-MOS, L
 Case: H9/a\$
 Prod.:
 Inr: International Rectifier Corporation

UDS: 250V
 UGS: $\pm 20V$
 ID: 14A
 IDM: 56A
 Ptot: 125W@Tg: 25°C
 RthG: 1°C/W
 RthU: 30°C/W
 Tj: 150°C

rds(on) typ: 0,25Ohm@UGS: 10V
 IDtyp: 8A
 Idss max: 0,25mA@UDS: max
 rds(on) max: 0,28Ohm@UGS: 10V
 Uth min: 2V@UDS: =UGSV ID: 250 μ A
 Uth max: 4V@UDS: =UGSV ID: 250 μ A
 gfs min: 6,7SmS@UDS: 50V ID: 8A
 gfs typ: 10SmS@UDS: 50V ID: 8A
 t_{on} max: 124ns
 t_{off} max: 154ns
 IGSS: $\pm 100nA$ @UGS: $\pm 20V$

M



H9

TO-3

Pin1: Source
 Pin2: Gate
 Pin3: Drain
 Drain + Case connected